



30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-90A

Features

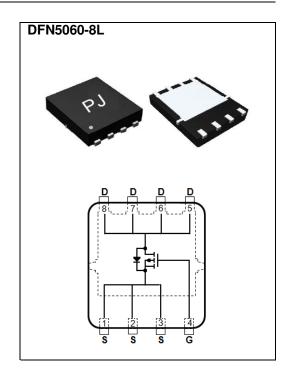
- $R_{DS(ON)}$, V_{GS} @-10V, I_D @-20A<4.5m Ω
- $R_{DS(ON)}$, V_{GS} @-4.5V, I_D @-15A<7 $m\Omega$
- · High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060-8L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	-30	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	٧	
Continuous Drain Current	T _C =25°C	I _D	-90	А	
	T _C =100°C		-57		
Pulsed Drain Current ^(Note 1)	T _C =25°C	I_{DM}	-360	ı	
Power Dissipation	T _C =25°C	Po	60	W	
	T _C =100°C		24		
Continuous Drain Current	T _A =25°C	I _D	-15.8	Α	
	T _A =70°C		-12.6	Α	
Power Dissipation	T _A =25°C		2	W	
Power Dissipation	T _A =70°C	Po	1.3		
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	2.1	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V,I _D =-250uA	-30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250$ uA	-1	-1.6	-2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-20A	-	3.9	4.5	mΩ
		V _{GS} =-4.5V,I _D =-15A	-	5.7	7	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =-30V, V_{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V ^(Note 2,3)	-	107	-	nC
Gate-Source Charge	Q_gs		-	18	-	
Gate-Drain Charge	Q_gd		-	18	-	
Input Capacitance	Ciss	V _{DS} =-25V, V _{GS} =0V, f=1.0MHZ	-	6067	-	pF
Output Capacitance	Coss		-	709	-	
Reverse Transfer Capacitance	Crss	I=1.0IVIITZ	-	361	-	
Turn-On Delay Time	td _(on)	\/ 4E\/ 4A	-	22	-	ns
Turn-On Rise Time	t _r	V_{DS} =-15V, I_{D} =-1A, V_{GS} =-10V, R_{G} =6 Ω (Note 2,3)	-	48	-	
Turn-Off Delay Time	td _(off)		-	197	-	
Turn-Off Fall Time	t _f		-	90	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					-90	Α
Diode Forward Current	I _S		-	-	-90	^
Diode Forward Voltage	V_{SD}	I _S =-1A,V _{GS} =0V	-	-0.68	-1	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing





TYPICAL CHARACTERISTIC CURVES

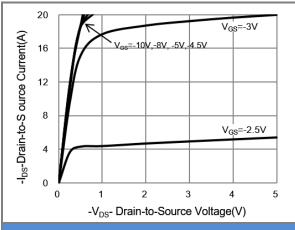


Fig.1 On-Region Characteristics

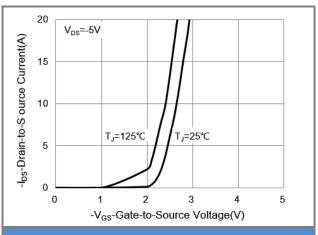


Fig.2 Transfer Characteristics

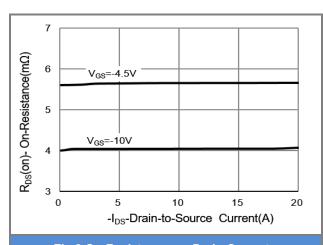


Fig.3 On-Resistance vs. Drain Current

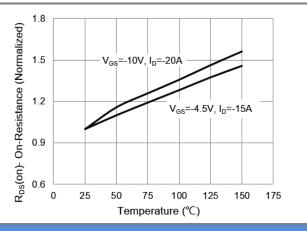


Fig.4 On-Resistance vs. Junction temperature

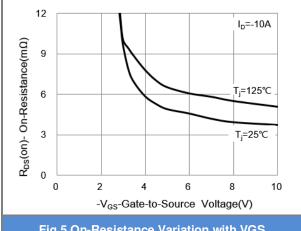


Fig.5 On-Resistance Variation with VGS.

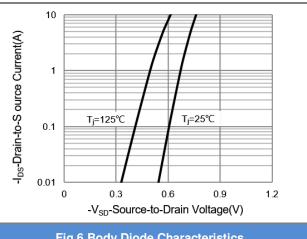


Fig.6 Body Diode Characteristics



1.2

1.0

8.0

0.6

0.4

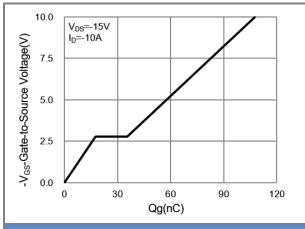
0

V_{TH}-G-S Vriance



PJQ5425

TYPICAL CHARACTERISTIC CURVES



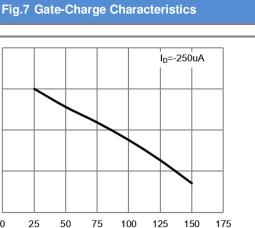


Fig.9 Threshold Voltage Variation with Temperature

Temperature (°C)

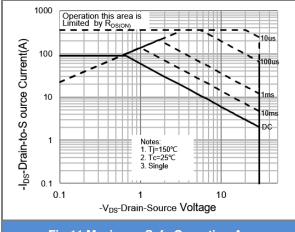


Fig.11 Maximum Safe Operating Area

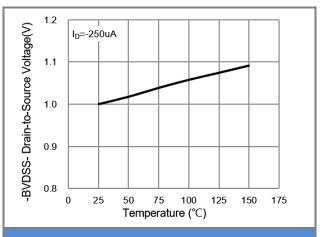


Fig.8 Breakdown Voltage Variation vs. Temperature

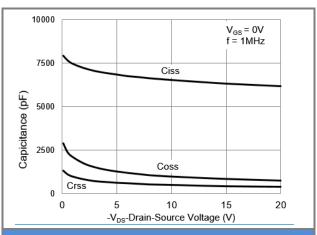


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

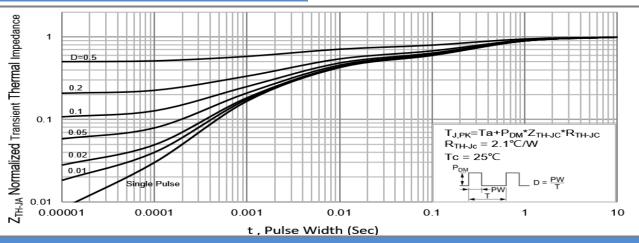


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

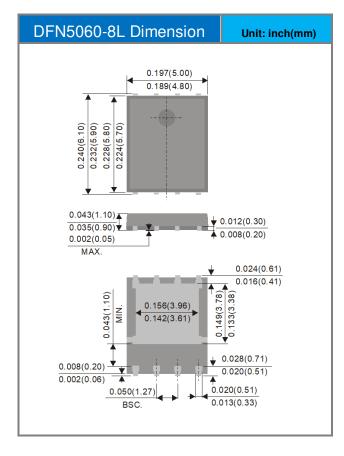


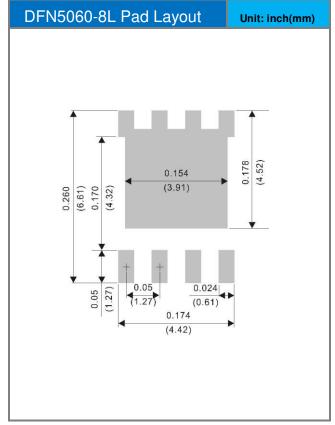


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5425_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5425	Halogen free	

Packaging Information & Mounting Pad Layout









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